

Amendments to the Claims

1. (Currently Amended): A method of depositing a silicon ~~dioxide~~ comprising dioxide-comprising layer in the fabrication of integrated circuitry, comprising:

flowing an ~~aluminum-containing~~ aluminum-containing organic precursor to a chamber containing a semiconductor substrate effective to deposit an ~~aluminum-comprising~~ aluminum-comprising layer over the substrate;

flowing an alkoxysilanol to the substrate comprising the ~~aluminum~~ comprising aluminum-comprising layer within the chamber effective to deposit a silicon ~~dioxide-comprising~~ dioxide-comprising layer over the substrate; and

providing at least one halogen within the chamber during at least one of the ~~aluminum-containing~~ aluminum-containing organic precursor flowing and the alkoxysilanol flowing under conditions effective to reduce rate of the deposit of the silicon ~~dioxide-comprising~~ dioxide-comprising layer over the substrate than would otherwise occur under identical conditions but for providing the at least one halogen.

2. (Currently Amended): The method of claim 1 wherein the ~~aluminum-containing~~ aluminum-containing organic precursor comprises a methyl aluminum.

3. (Currently Amended): The method of claim 1 wherein the ~~aluminum-comprising~~ aluminum-comprising layer comprises an aluminum compound.
4. (Original): The method of claim 3 wherein the aluminum compound comprises a methyl aluminum.
5. (Original): The method of claim 3 wherein the aluminum compound comprises an aluminum oxide.
6. (Original): The method of claim 3 wherein the aluminum compound comprises a methyl aluminum oxide.
7. (Currently Amended): The method of claim 1 wherein the ~~aluminum-comprising~~ aluminum-comprising layer is no more than 3 monolayers thick.
8. (Original): The method of claim 1 wherein the alkoxysilanol comprises tristertbutoxysilanol.
9. (Original): The method of claim 1 wherein the alkoxysilanol comprises tristertpentoxysilanol.

10. (Original): The method of claim 1 wherein the halogen is provided during the alkoxysilanol flowing.

11. (Currently Amended): The method of claim 1 wherein the halogen is provided by flowing a ~~halogen-containing~~ halogen-containing precursor to the chamber while flowing the alkoxysilanol.

12. (Original): The method of claim 1 wherein the halogen is provided from deposited material on the substrate which contains the halogen.

13. (Currently Amended): The method of claim 1 wherein the ~~silicon dioxide-comprising~~ dioxide-comprising layer is formed in a blanketing manner on the substrate.

14. (Currently Amended): The method of claim 1 wherein the ~~silicon dioxide-comprising~~ dioxide-comprising layer is selectively formed on some areas of the substrate versus other areas of the substrate.

15. (Original): The method of claim 1 wherein said flowing of alkoxysilanol is continuous.

16. (Original): The method of claim 1 wherein said flowing of alkoxysilanol is continuous at a substantially constant rate.

17. (Original): The method of claim 1 wherein said flowing of alkoxysilanol is pulsed.

18. (Original): The method of claim 1 wherein the halogen comprises fluorine.

19. (Original): The method of claim 1 wherein the halogen comprises chlorine.

20. (Original): The method of claim 1 wherein the halogen comprises bromine.

21. (Original): The method of claim 1 wherein the halogen comprises iodine.

Claims 22-99 (Canceled).